

HD74HC1G66

Analog Switch

REJ03D0188-0800Z (Previous ADE-205-314F (Z)) Rev.8.00 Jan.27.2004

Description

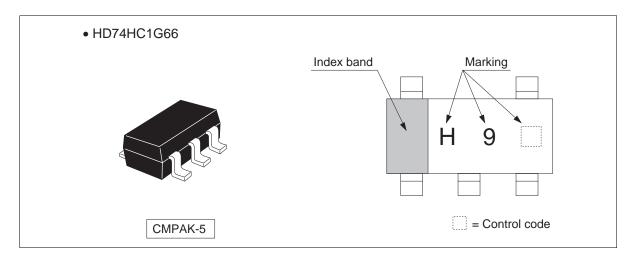
The HD74HC1G66 is high-speed CMOS analog switch using silicon gate CMOS process. With CMOS low power dissipation, it provides high speed. The device has low ON resistance for good transfer characteristics and can take wide range of input voltage.

Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the HD74HC4066 Supply voltage range: 2 to 6 V
 Operating temperature range: -40 to +85°C
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)	
HD74HC1G66CME	CMPAK-5 pin	CMPAK-5A	CM	E (3,000 pcs/reel)	

Outline and Article Indication

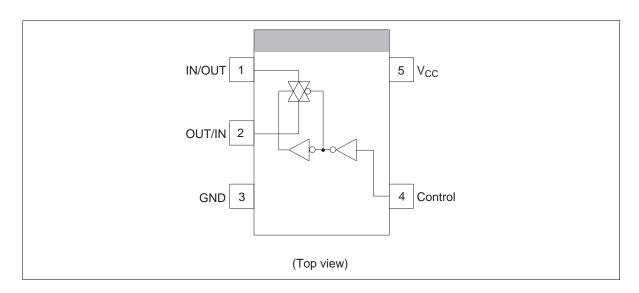


Function Table

Control	Switch
L	OFF
Н	ON

H: High level
L: Low level
GND \leq V_{IN} \leq V_{CC}
GND \leq V_{OUT} \leq V_{CC}

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions		
Supply voltage range	V _{CC}	-0.5 to 7.0	V			
Input voltage range *1	Vı	-0.5 to V _{CC} + 0.5	V			
Output voltage range *1,2	Vo	-0.5 to V _{CC} + 0.5	V	Output : H or L		
Input clamp current	I _{IK}	±20	mA	$V_I < 0$ or $V_I > V_{CC}$		
Output clamp current	I _{OK}	±20	mA	$V_O < 0$ or $V_O > V_{CC}$		
Continuous output current	Io	±25	mA	$V_{\rm O}$ = 0 to $V_{\rm CC}$		
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±25	mA			
Maximum power dissipation at Ta = 25°C (in still air) *3	P _T	200	mW			
Storage temperature	Tstg	-65 to 150	°C			

Notes:

- The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.
- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Symbol	Min	Max	Unit	Test Conditions
V _{CC}	2	6	V	
V _{I/O}	0	V _{CC}	V	
Vo	0	Vcc	V	
t_r, t_f	0	1000	ns	V _{CC} = 2.0 V
	0	500		V _{CC} = 4.5 V
	0	400		V _{CC} = 6.0 V
Та	-40	85	°C	
	V _{I/O} Vo t _r , t _f	$\begin{array}{ccc} V_{I/O} & 0 \\ V_O & 0 \\ t_r, t_f & 0 \\ \hline 0 & 0 \\ \end{array}$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

Note: Unused or floating control inputs must be held high or low.

HD74HC1G66

Electrical Characteristics

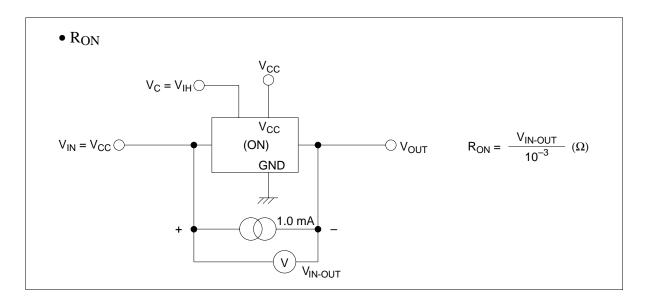
		\mathbf{V}_{CC}	Ta = 25°C		Ta = −40 to 85°C					
Item	Symbo	(V)	Min	Тур	Max	Min	Max	Unit	Test Conditions	
Input voltage	V _{IH}	2.0	1.5	_	_	1.5	_	V	Control input only	
		4.5	3.15	_	_	3.15	_			
		6.0	4.2	_	_	4.2	_	_		
	V _{IL}	2.0	_	_	0.5	_	0.5	_		
		4.5	_	_	1.35	_	1.35	_		
		6.0	_	_	1.8	_	1.8	_		
On resistance	R _{ON}	2.0	_	200	450	_	550	Ω -	$V_C = V_{IH}$	
		4.5	_	90	160	_	180		$V_{IN} = V_{CC}$ or GND $I_T = 1 \text{ mA}$	
		6.0	_	80	130	_	140			
Peak on	R _{ON} (p)	2.0	_	600	1500	_	2000	- V _{II}	V _C = V _{IH}	
resistance		4.5	_	125	200	_	250		$V_{IN} = 0$ to V_{CC} $I_{IN/OUT} = 1$ mA	
		6.0	_	100	170	_	210		IIN/OUT - I IIIA	
Leak current	I _S (off)	6.0	_	_	±0.1	_	±1.0	μА	$\begin{aligned} &V_{C} = V_{IL} \\ &V_{IN} = V_{CC}, V_{OUT} = GND \\ &\text{or } V_{IN} = GND, \\ &V_{OUT} = V_{CC} \end{aligned}$	
	I _S (on)	6.0	_	_	±0.1	_	±1.0	μΑ	$V_C = V_{IH}$ $V_{IN} = V_{CC}$ or GND	
Input current	I _{IN}	6.0	_	_	±0.1	_	±1.0	μΑ	V _{IN} = V _{CC} or GND	
Operating current	I _{CC}	6.0	_	_	1.0	_	10.0	μΑ	V _{IN} = V _{CC} or GND	

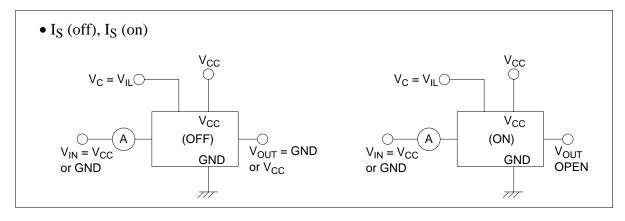
Switching Characteristics

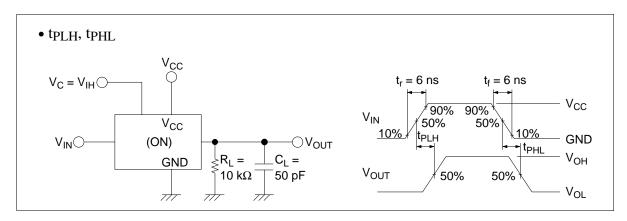
		\mathbf{V}_{CC}	Ta = 25° C Ta = -40 to 85° C		0 to 85°C				
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Propagation delay time	t _{PLH} ,	2.0	_	_	50	_	65	ns	R_L = 10 $k\Omega$
	t _{PHL}	4.5	_	4	10	_	13	-	
		6.0	_	_	9	_	11	-	
Output enable time	t_{ZH}, t_{ZL}	2.0	_	_	115	_	145	ns	$R_L = 1 k\Omega$
		4.5	_	10	23	_	29	-	
		6.0	_	_	20	_	25	-	
Output disable time	t_{HZ},t_{LZ}	2.0	_	_	115	_	145	ns	$R_L = 1 k\Omega$
		4.5	_	14	23	_	29	-	
		6.0	_	_	20	_	25	-	
Maximum control		2.0	_	20	_	_	_	MHz	
frequency		4.5	_	30	_	_	_	-	
		6.0	_	30	_	_	_	-	
Control input capacitance	C _{IN}		_	2.5	5	_	5	pF	
Switch I/O capacitance	C _{IN/OUT}		_	2.5	_	_	_	pF	
Feed through capacitance	C _{IN-OUT}		_	0.5	_	_	_	pF	
Power dissipation capacitance	C_{PD}		_	5	_	_	_	pF	

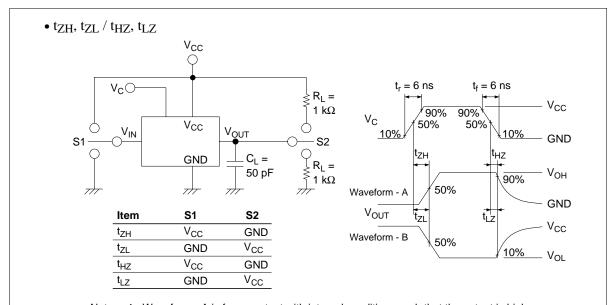
 $⁽C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns})$

Test Circuit



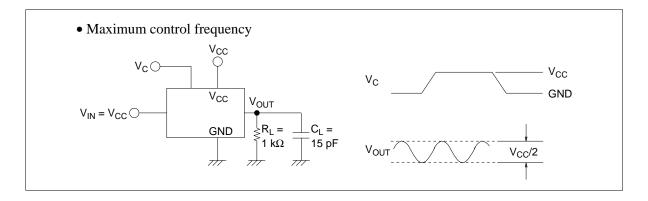


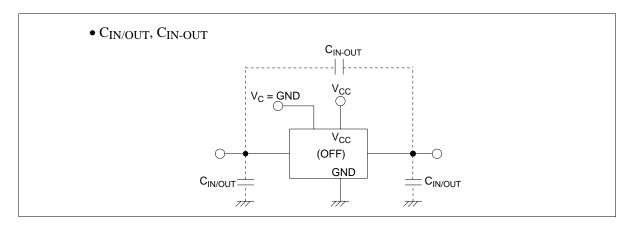




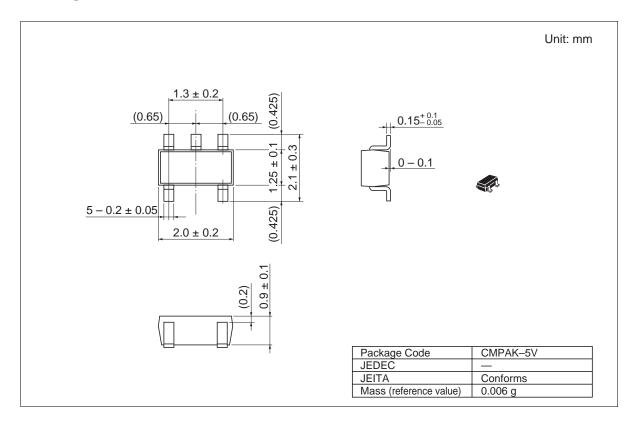
Notes: 1. Waveform - A is for an output with internal conditions such that the output is high except when disabled by the output control.

2. Waveform - B is for an output with internal conditions such that the output is low except when disabled by the output control.





Package Dimensions



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